

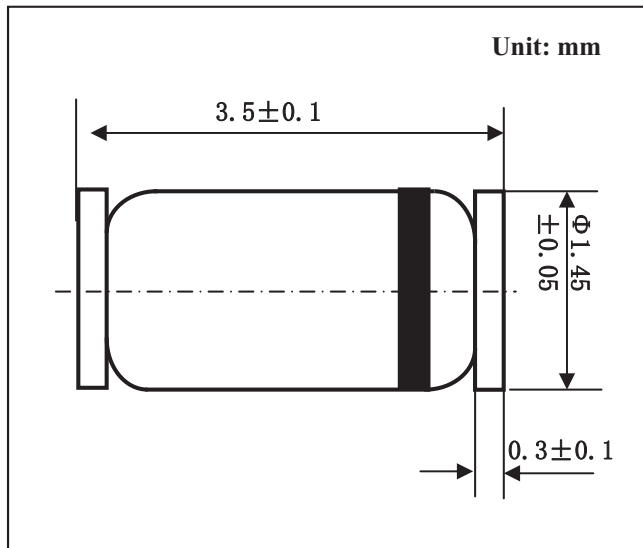
LL34 SILICON BIDIRECTIONAL DIACS

FEATURES

- Fast Switching Speed
- Electrically Identical to Standard JEDEC
- High reliability
- Lead free in compliance with EU RoHS 2.0
- Component in accordance to RoHS 2015/863 and WEEE 2012/19/EU

MECHANICAL DATA

- Case style: LL34, glass case
- Mounting position: Any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Power Dissipation	Pd	350	mW
Storage temperature	Ts	-40-+150	°C
Operating Junction Temperature	Tj	100	°C

Notes: The glass passivated, three-layer, two terminal, axial lead, hermetically sealed diacs are designed specifically for triggering thyristors. They demonstrate low breakover current at breakover voltage as they withstand peak pulse current. The breakover symmetry is within four bolts with a typical breakover voltage of 32 volts. These diacs are intended for use in thyristor phase control, circuits for lamp-dimming, universal-motor speed controls, and heat controls.

Test	Symbol	Min	Typ.	Max.	Unit
Breakover Voltage	VBO1&VBO2	28	32.0	36	V
Breakover Currents	IBO1&IBO2	-	-	200	uA
Breakover Voltage Symmetry	VBO1 - VBO2	-	-	3.8	V
Dynamic Breakover Voltage $\Delta I=[IBO \text{ to } IF = 10mA]$	$ \pm \Delta V $	5	-	-	V
Thermal Impedance Junction To Ambient	R Φ JA	-	-	60	°C/W

RATINGS AND CHARACTERISTIC CURVES

FIG.1–VOLTAGE-CURRENT CHARACTERISTIC CURVE

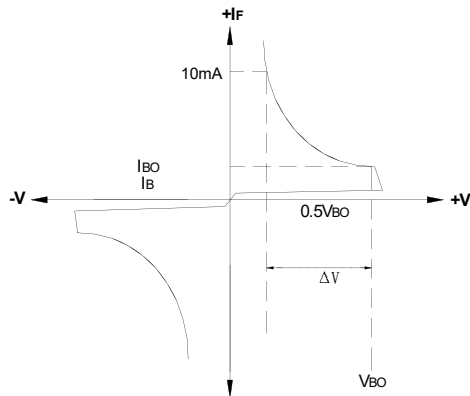


FIG.2–TEST CIRCUIT FOR OUTPUT VOLTAGE

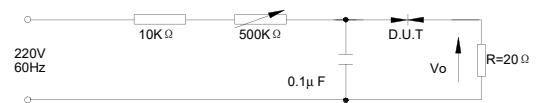


FIG.3– TEST CIRCUIT SEE FIG.2 ADJUST R FOR $I_P=0.5A$

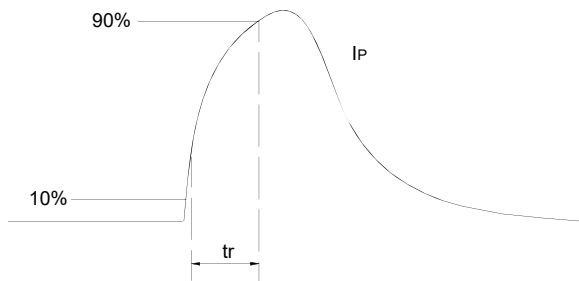


FIG.5–RELATIVE VARIATION OF V_{BO} VERSUS JUNCTION TEMPERATURE(TYPICAL VALUES)

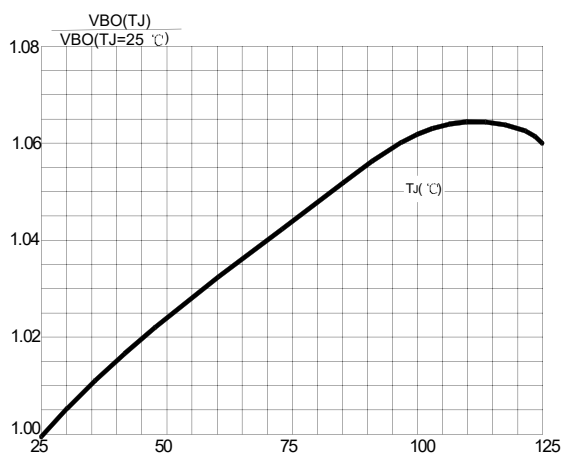


FIG.4–POWER DISSIPATION VERSUS AMBIENT TEMPERATURE (MAXIMUM VALUES)

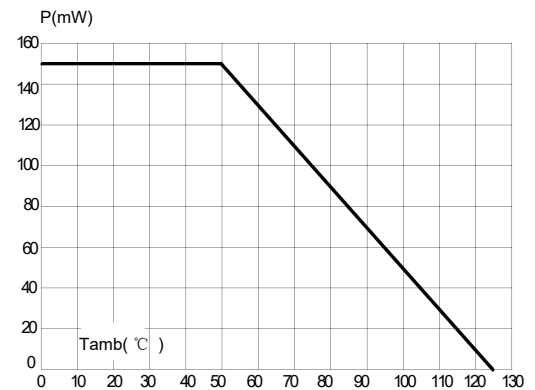


FIG.6–PEAK PULSEE CURRENT VERENT VERSUS PULSE DURATION(MAXIMUM VALUES)

